

Industrial Grade Low-Skew, 1-to-2 LVCMOS/LVTTL Fanout Buffer

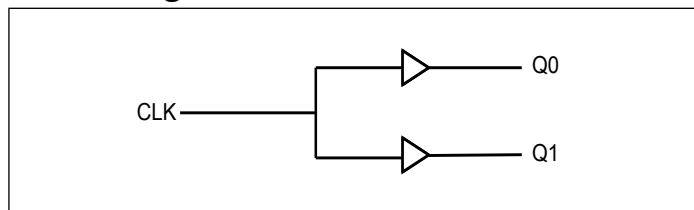
Features

- Two LVCMOS/LVTTL Outputs
- LVCMOS/LVTTL Clock Input Accepts LVCMOS or LVTTL Input Levels
- Maximum Output Frequency: 250MHz
- Output Skew: 25ps (Typical)
- Full 3.3V, 2.5V Operation Modes
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free “Green” Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative.
<https://www.diodes.com/quality/product-definitions/>
- Packaging (Pb-free & Green):
 - Small 8-pin SOIC (W) package saves board space

Description

The PI6C49CB02J is an industrial grade low-skew, 1-to-2 LVCMOS/LVTTL high-performance fanout buffer. The PI6C49CB02J has a single-ended clock input. The single-ended clock input accepts LVCMOS or LVTTL input levels. The PI6C49CB02J features a pair of LVCMOS/LVTTL outputs. Guaranteed output and part-to-part skew characteristics make the PI6C49CB02J ideal for clock distribution applications demanding well-defined performance and repeatability.

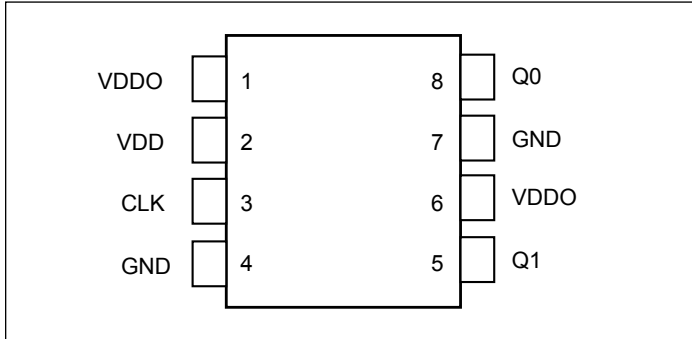
Block Diagram



Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated’s definitions of Halogen- and Antimony-free, “Green” and Lead-free.
3. Halogen- and Antimony-free “Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Pin Configuration



Pin Descriptions

Pin#	Pin Name	Pin Type		Pin Description
1, 6	VDDO	Power	—	Output Supply Pins
2	VDD	Power	—	Core Supply Pin
3	CLK	Input	Pull-down	LVC MOS/LVTTL Clock Input
4, 7	GND	Power	—	Power Supply Ground
5	Q1	Output	—	Single Clock Output. LVC MOS/LVTTL Interface Levels.
8	Q0	Output	—	Single Clock Output. LVC MOS/LVTTL Interface Levels.

Note: *Pull-down* refer to internal input resistors, typical values in Pin Characteristics table.

Pin Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
C_N	Capacitance	—	—	4	—	pF
$R_{PULLDOWN}$	Input Pull-down Resistor	—	—	51	—	k Ω
R_{OUT}	Output Impedance	—	5	7	12	Ω

Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Maximum Supply Voltage, VDD, VDDO	4.6V
Inputs, V_I	-0.5V to VDD+0.5V
Output, V_O	-0.5V to VDDO+0.5V
Storage Temperature	-65°C to 150°C
ESD Protection (HBM)	2000V
Junction Temperature	125°C (Max)

Note:

Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the DC Characteristics or AC Characteristics is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Recommended Operation Conditions

Parameter	Min.	Typ.	Max.	Units
Ambient Operating Temperature	-40	—	+105	°C
Power Supply Voltage (measured in respect to GND)	+2.375	—	+3.465	V

Power Supply DC Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
VDD	Core Supply Voltage	3.3V Operation	3.135	3.3	3.465	V
		2.5V Operation	2.375	2.5	2.625	
VDDO	Output Power Supply Voltage	3.3V Supply	3.135	3.3	3.465	V
		2.5V Supply	2.375	2.5	2.625	
IDD	Power Supply Current	$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	—	—	5	mA
IDDO	Output Supply Current	Unloaded, 25 MHz, $T_A = -40^\circ\text{C to } 85^\circ\text{C}$	—	—	6.5	mA
IDD	Power Supply Current	$T_A = -40^\circ\text{C to } 105^\circ\text{C}$	—	—	5	mA
IDDO	Output Supply Current	Unloaded, 25 MHz, $T_A = -40^\circ\text{C to } 105^\circ\text{C}$	—	—	6.5	mA

Note: Parameters measured up to f_{max} unless otherwise noted.

LVC MOS / LV TTL DC Characteristics, $T_A = -40^{\circ}\text{C}$ to 105°C

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
V_{IH}	Input High Voltage	VDD = 3.3V	2	—	VDD+0.3	V
		VDD = 2.5V	1.7	—	VDD+0.3	
V_{IL}	Input Low Voltage	VDD = 3.3V	-0.3	—	0.8	V
		VDD = 2.5V	-0.3	—	0.8	
I_{IH}	Input High Current	VDD = $V_{IN} = 3.465\text{V}$	—	—	100	μA
		VDD = $V_{IN} = 2.625\text{V}$	—	—	80	
I_{IL}	Input Low Current	VDD = 3.465V, $V_{IN} = 0\text{V}$	-5	—	—	μA
		VDD = 2.625V, $V_{IN} = 0\text{V}$	-5	—	—	
V_{OH}	Output High Voltage	VDDO = 3.3V $I_{OH} = -100\mu\text{A}$	2.9	—	—	V
		VDDO = 2.5V $I_{OH} = -100\mu\text{A}$	2.2	—	—	V
V_{OL}	Output Low Voltage	VDDO = 3.3V $I_{OL} = 100\mu\text{A}$	—	—	0.2	V
		VDDO = 2.5V $I_{OL} = 100\mu\text{A}$	—	—	0.2	V

AC Characteristics, VDD = 3.3V ± 5%, T_A = -40°C to 105°C

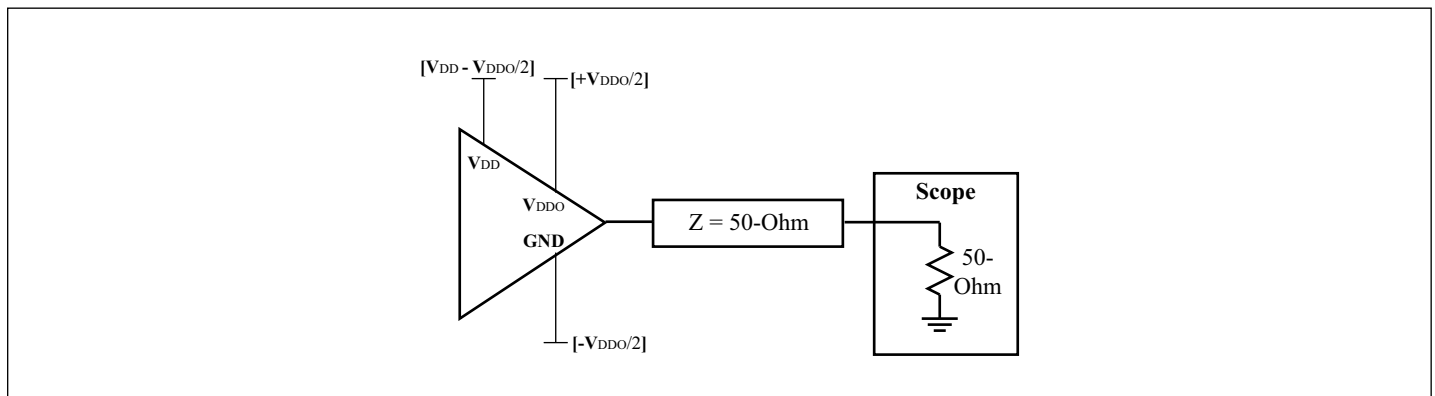
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
f _{MAX}	Output Frequency	VDDO = 3.3V	4	—	250	MHz
		VDDO = 2.5V	4	—	250	
t _{pLH}	Propagation Delay, Low-to-High ⁽¹⁾	VDDO = 3.3V, f ≤ 250MHz	1.4	—	2.2	ns
		VDDO = 2.5V, f ≤ 250MHz	1.5	—	3.0	
tsk(o)	Output Skew ⁽²⁾	—	—	25	80	ps
tsk(pp)	Part-to-Part Skew ⁽³⁾	—	—	250	800	ps
t _R	Output Rise Time ⁽⁴⁾	VDDO = 3.3V	100	300	400	ps
		VDDO = 2.5V	100	350	500	
t _F	Output Fall Time ⁽⁴⁾	VDDO = 3.3V	100	300	400	ps
		VDDO = 2.5V	100	350	500	
odc	Output Duty Cycle ⁽⁵⁾	f ≤ 133MHz	48	—	52	%
		133MHz < f ≤ 200MHz	47	—	53	%
		200MHz < f ≤ 250MHz	47	—	53	%
t _{jit}	Additive RMS Jitter	156.25MHz (@12kHz to 20MHz)	—	0.1	—	ps
		125MHz (@12kHz to 20MHz)	—	0.07	—	ps

Note:

Parameters measured at f_{MAX} unless otherwise noted.

1. Measured from VDD/2 of the input to VDDO/2 of the output.
2. Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at VDDO/2.
3. Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at VDDO/2.
4. Defined from 20% to 80%.
5. Measured at VDDO/2.

AC Test Circuit Load



AC Characteristics, VDD = 2.5V ± 5%, T_A = -40°C to 105°C

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
f _{MAX}	Output Frequency	VDDO = 2.5V	4	—	250	MHz
t _{pLH}	Propagation Delay, Low-to-High ⁽¹⁾	VDDO = 2.5V, f ≤ 250MHz	1.5	—	2.8	ns
t _{sk(o)}	Output Skew ⁽²⁾	—	—	25	75	ps
t _{sk(pp)}	Part-to-Part Skew ⁽³⁾	—	—	250	800	ps
t _R	Output Rise Time ⁽⁴⁾	VDDO = 2.5V	100	350	500	ps
t _F	Output Fall Time ⁽⁴⁾	VDDO = 2.5V	100	350	500	ps
odc	Output Duty Cycle ⁽⁵⁾	f ≤ 133MHz	48	—	52	%
		133MHz < f ≤ 200MHz	47	—	53	%
		200MHz < f ≤ 250MHz	42	—	58	%
t _{jit}	Additive RMS Jitter	156.25MHz (@12kHz to 20MHz)	—	0.1	—	ps
		125MHz (@12kHz to 20MHz)	—	0.07	—	ps

Note:

Parameters measured at f_{MAX} unless otherwise noted.

1. Measured from VDD/2 of the input to VDDO/2 of the output.
2. Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at VDDO/2.
3. Defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at VDDO/2.
4. Defined from 20% to 80%.
5. Measured at VDDO/2.

Part Marking

PI6C49C
B02JWE
YYWWXX
○

- YY: Year
- WW: Workweek
- 1st X: Assembly Code
- 2nd X: Fab Code

PI6C49CB02J

Packaging Mechanical: 8-SOIC (W)

SYMBOLS	MIN.	NOM.	MAX.
A	—	—	1.75
A1	0.10	—	0.25
A2	1.25	—	—
b	0.31	—	0.51
c	0.10	—	0.25
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e	1.27 BSC		
L	0.40	—	1.27
h	0.25	—	0.50
θ°	0	—	8

NOTE:
 1. ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES
 2. DIMENSIONS EXCLUDE BURRS, MOLD FLASH OR PROTRUSIONS
 3. REFER JEDEC MS-012
 4. RECOMMENDED LAND PATTERN IS FOR REFERENCE ONLY.

20-1273

DIODES **PERICOM** ENABLING SERIAL CONNECTIVITY **DATE: 06/02/20**

DESCRIPTION: 8-Pin, 150mil-Wide, SOIC

PACKAGE CODE: W (W8)

DOCUMENT CONTROL #: PD-1001 **REVISION: H**

For latest package information:

See <http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/>.

Ordering Information

Ordering Code	Package Code	Package Description
PI6C49CB02JWEX	W	8-pin, 150mil-Wide (SOIC)

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. J = Industrial Grade
5. E = Pb-free and Green
6. X suffix = Tape/Reel

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